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Tech ID: 33098

ADDITIONAL TECHNOLOGIES BY THESE INVENTORS

- ▶ Vertical Cavity Surface-Emitting Lasers with Continuous Wave Operation
- ▶ Eliminating Misfit Dislocations with In-Situ Compliant Substrate Formation
- ▶ III-Nitride-Based Vertical Cavity Surface Emitting Laser (VCSEL) with a Dielectric P-Side Lens
- ► Ultraviolet Laser Diode on Nano-Porous AlGaN template
- Improved Fabrication of Nonpolar InGaN Thin Films, Heterostructures, and Devices
- ► Methods for Fabricating III-Nitride Tunnel Junction Devices
- ► Contact Architectures for Tunnel Junction Devices
- ▶ III-Nitride Tunnel Junction LED with High Wall Plug Efficiency
- Novel Multilayer Structure for High-Efficiency UV and Far-UV Light-Emitting Devices
- ▶ A Method To Lift-Off Nitride Materials With Electrochemical Etch
- ► High-Intensity Solid State White Laser Diode
- ▶ Nitride Based Ultraviolet LED with an Ultraviolet Transparent Contact
- ▶ High-Efficiency and High-Power III-Nitride Devices Grown on or Above a Strain Relaxed Template
- ► III-Nitride Based VCSEL with Curved Mirror on P-Side of the Aperture

